



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

SURFACE MOUNT SCHOTTKY DIODE

VOLTAGE 40 Volts CURRENT 0.2 Ampere

BAS40TPT

APPLICATION

* Ultra high speed switching

FEATURE

- * Small surface mounting type. (SC-75/SOT-416)
- * High speed. ($T_{RR}=2.5nSec$ Typ.)
- * Suitable for high packing density.
- * Maximum total power dissipation is 200mW.
- * Peak forward current is 300mA.

CONSTRUCTION

* Silicon epitaxial planar

WEIGHT

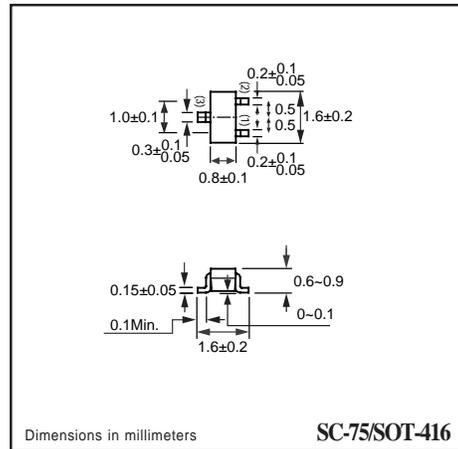
* 0.006 grams (Approx.)

MARKING

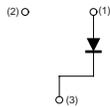
* TO



SC-75/SOT-416



CIRCUIT



RATINGS	SYMBOL	BAS40TPT	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	40	Volts
Maximum RMS Voltage	VRMS	28	Volts
Maximum DC Blocking Voltage	VDC	40	Volts
Maximum Average Forward Rectified Current	IO	0.2	Amps
Peak Forward Surge Current at 1Sec.	IFSM	0.6	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	5.0	pF
Maximum Reverse Recovery Time (Note 2)	TRR	5.0	nSec
Maximum Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	TSTG	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	BAS40TPT	UNITS
Maximum Instantaneous Forward Voltage	@If= 1.0mA	380	mVolts
	@If= 40mA	1000	
Maximum Average Reverse Current at VR= 30V	IR	200	nAmps

- NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0.0 volts.
 2. Measured at applied forward current of 10mA and reverse current of 10mA.
 3. ESD sensitive product handling required.

2004-06

RATING CHARACTERISTIC CURVES (BAS40TPT)

FIG. 1 - FORWARD CHARACTERISTICS

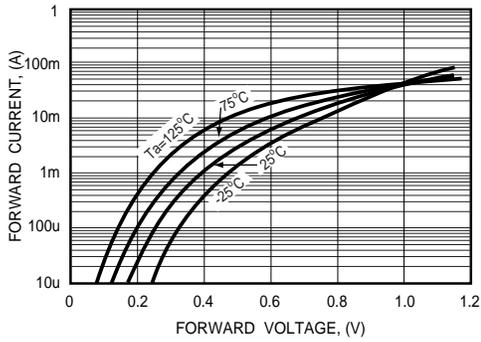


FIG. 2 - REVERSE CHARACTERISTICS

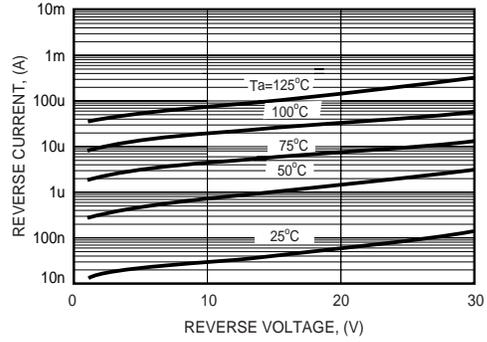


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

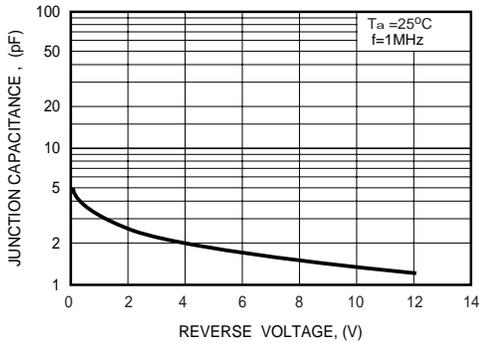


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

